**PATENT** 

APR 3 0 1907

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Wu et al.

Attorney Docket No.:

NOVLP097/NVLS-2906

Application No.: 10/807,680

Examiner: Not yet assigned

Filed: March 23, 2004

Group: 2812

Title: METHODS OF POROGEN REMOVAL FOR POROUS LOW DIELECTRIC

FOR POROUS LOW DIELECTRIC CONSTANT FILMS USING PLASMA

**TREATMENTS** 

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail on April 97, 2007in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 223 14-1450.

Signed:

Tara Hayden

INFORMATION DISCLOSURE STATEMENT 37 CFR §§1.56 AND 1.97(b)

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, copies of which are attached, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP097).

Respectfully submitted,

BEYER WEAVER LLP

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Registration No. 50,581

APR 3 0 7007

Application No.:
NOVLP097/ NVLS-2906
Information Disclosure
Statement By Applicant

Wu et al.
Filing Date
(Use Several Sheets if Necessary)

March 23, 2004

Application No.:
NOVLP097/ NVLS-2906

Applicant:
Wu et al.
Filing Date
Group
March 23, 2004

2812

## **U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
	Al	7,094,713 B1	08.22.06	Niu et al.			
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## Other Documents

		Other Documents				
Examiner						
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication				
	C1	U.S. Office Action mailed December 27, 2006, from U.S Application No. 10/825,8				
		[Atty Dkt No. NOVLP088/NVLS-2882].				
	C2	Cho et al., "Method and Apparatus for UV Exposure of Low Dielectric Constant				
		Materials for Porogen Removal and Improved Mechanical Properties", Novellus				
		Systems, Inc., Application No. 11/656,661, filed January 22, 2007, pages 1-28.				
		[Atty. Docket No. NOVLP089D1/NVLS-2887D1]				
	C3	Shrinivasan et al., "Single-Chamber Sequential Curing of Semiconductor Wafers,"				
		Novellus Systems, Inc., Application No. 11/115,576, filed April 26, 2005, pages 1-				
		29. [NOVLP127/NVLS-3044]				
	C4	Kamian et al., "Ultra Violet Light Treatment Load Lock for Dielectric Films,"				
		Novellus Systems, Inc., Application No. 11/561,834, filed November 20, 2006, pages				
		1-25. [NOVLP184/NVLS-3109]				
	C5	Schravendijk et al., "UV Treatment of Etch Stop and Hard Mask Films for Selectivity				
		and Hermeticity Enhancement," Novellus Systems, Inc., Application No. 11/696,102,				
	ļ	filed April 3, 2007, pages 1-22. [NOVLP191/NVLS-3218]				
	C6	Vancouver et al., "PECVD Methods for Producing Ultra Low-K Dielectric Films				
		Using UV Treatment," Application No. 11/608,056, filed December 7, 2006, pages 1-				
		34. [NOVLP196/NVLS-3238]				
	C7	Tarafdar et al., "Sequential Deposition/Anneal Film Densification Method", Novellus				
		Systems, Inc., filed September 11, 2006, Application No. 11/519,445, pages 1-37.				
		[Atty Dckt. NOVLP116X1/NVLS-2975C1]				
	C8	Schravendijk, "UV Treatment of FSG Films to Improve Film Stability," Novellus				
		Systems, Inc., Application No. 11/622,423, filed January 11, 2007, pages 1-31.				
		[NOVLP189/NVLS-3215]				
Examiner	<del></del>	Date Considered				

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.